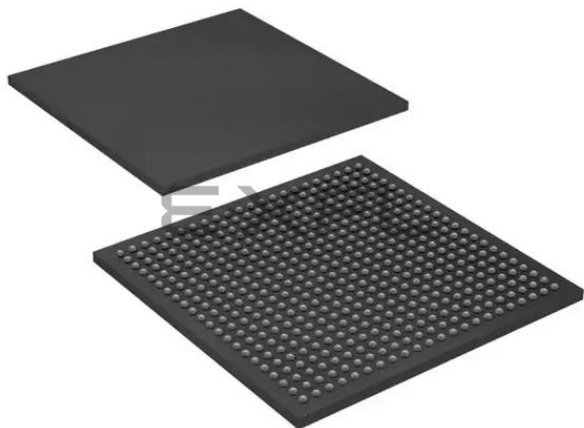




Welcome to [E-XFL.COM](#)

Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	360
Number of Logic Elements/Cells	2880
Total RAM Bits	40960
Number of I/O	220
Number of Gates	199000
Voltage - Supply	2.3V ~ 2.7V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	484-BBGA
Supplier Device Package	484-FBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epf10k50efc484-2



For more information on FLEX device configuration, see the following documents:

- *Configuration Devices for APEX & FLEX Devices Data Sheet*
- *BitBlaster Serial Download Cable Data Sheet*
- *ByteBlasterMV Parallel Port Download Cable Data Sheet*
- *MasterBlaster Download Cable Data Sheet*
- *Application Note 116 (Configuring APEX 20K, FLEX 10K, & FLEX 6000 Devices)*

FLEX 10KE devices are supported by the Altera development systems, which are integrated packages that offer schematic, text (including AHDL), and waveform design entry, compilation and logic synthesis, full simulation and worst-case timing analysis, and device configuration. The Altera software provides EDIF 2 0 0 and 3 0 0, LPM, VHDL, Verilog HDL, and other interfaces for additional design entry and simulation support from other industry-standard PC- and UNIX workstation-based EDA tools.

The Altera software works easily with common gate array EDA tools for synthesis and simulation. For example, the Altera software can generate Verilog HDL files for simulation with tools such as Cadence Verilog-XL. Additionally, the Altera software contains EDA libraries that use device-specific features such as carry chains, which are used for fast counter and arithmetic functions. For instance, the Synopsys Design Compiler library supplied with the Altera development system includes DesignWare functions that are optimized for the FLEX 10KE architecture.

The Altera development system runs on Windows-based PCs and Sun SPARCstation, and HP 9000 Series 700/800.



See the *MAX+PLUS II Programmable Logic Development System & Software Data Sheet* and the *Quartus Programmable Logic Development System & Software Data Sheet* for more information.

Embedded Array Block

The EAB is a flexible block of RAM, with registers on the input and output ports, that is used to implement common gate array megafunctions. Because it is large and flexible, the EAB is suitable for functions such as multipliers, vector scalars, and error correction circuits. These functions can be combined in applications such as digital filters and microcontrollers.

Logic functions are implemented by programming the EAB with a read-only pattern during configuration, thereby creating a large LUT. With LUTs, combinatorial functions are implemented by looking up the results, rather than by computing them. This implementation of combinatorial functions can be faster than using algorithms implemented in general logic, a performance advantage that is further enhanced by the fast access times of EABs. The large capacity of EABs enables designers to implement complex functions in one logic level without the routing delays associated with linked LEs or field-programmable gate array (FPGA) RAM blocks. For example, a single EAB can implement any function with 8 inputs and 16 outputs. Parameterized functions such as LPM functions can take advantage of the EAB automatically.

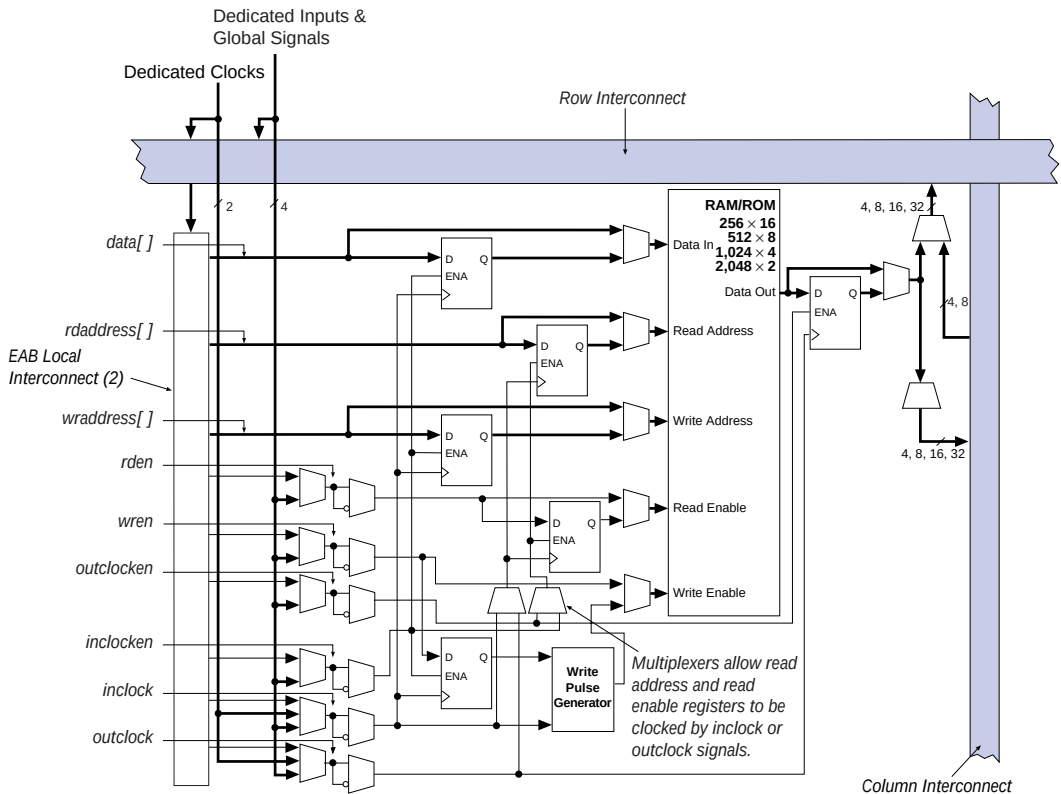
The FLEX 10KE EAB provides advantages over FPGAs, which implement on-board RAM as arrays of small, distributed RAM blocks. These small FPGA RAM blocks must be connected together to make RAM blocks of manageable size. The RAM blocks are connected together using multiplexers implemented with more logic blocks. These extra multiplexers cause extra delay, which slows down the RAM block. FPGA RAM blocks are also prone to routing problems because small blocks of RAM must be connected together to make larger blocks. In contrast, EABs can be used to implement large, dedicated blocks of RAM that eliminate these timing and routing concerns.

The FLEX 10KE enhanced EAB adds dual-port capability to the existing EAB structure. The dual-port structure is ideal for FIFO buffers with one or two clocks. The FLEX 10KE EAB can also support up to 16-bit-wide RAM blocks and is backward-compatible with any design containing FLEX 10K EABs. The FLEX 10KE EAB can act in dual-port or single-port mode. When in dual-port mode, separate clocks may be used for EAB read and write sections, which allows the EAB to be written and read at different rates. It also has separate synchronous clock enable signals for the EAB read and write sections, which allow independent control of these sections.

The EAB can also be used for bidirectional, dual-port memory applications where two ports read or write simultaneously. To implement this type of dual-port memory, two EABs are used to support two simultaneous read or writes.

Alternatively, one clock and clock enable can be used to control the input registers of the EAB, while a different clock and clock enable control the output registers (see Figure 2).

Figure 2. FLEX 10KE Device in Dual-Port RAM Mode Notes (1)



Notes:

- (1) All registers can be asynchronously cleared by EAB local interconnect signals, global signals, or the chip-wide reset.
- (2) EPF10K30E and EPF10K50E devices have 88 EAB local interconnect channels; EPF10K100E, EPF10K130E, and EPF10K200E devices have 104 EAB local interconnect channels.

Clearable Counter Mode

The clearable counter mode is similar to the up / down counter mode, but supports a synchronous clear instead of the up / down control. The clear function is substituted for the cascade-in signal in the up / down counter mode. Use 2 three-input LUTs: one generates the counter data, and the other generates the fast carry bit. Synchronous loading is provided by a 2-to-1 multiplexer. The output of this multiplexer is ANDed with a synchronous clear signal.

Internal Tri-State Emulation

Internal tri-state emulation provides internal tri-states without the limitations of a physical tri-state bus. In a physical tri-state bus, the tri-state buffers' output enable (OE) signals select which signal drives the bus. However, if multiple OE signals are active, contending signals can be driven onto the bus. Conversely, if no OE signals are active, the bus will float. Internal tri-state emulation resolves contending tri-state buffers to a low value and floating buses to a high value, thereby eliminating these problems. The Altera software automatically implements tri-state bus functionality with a multiplexer.

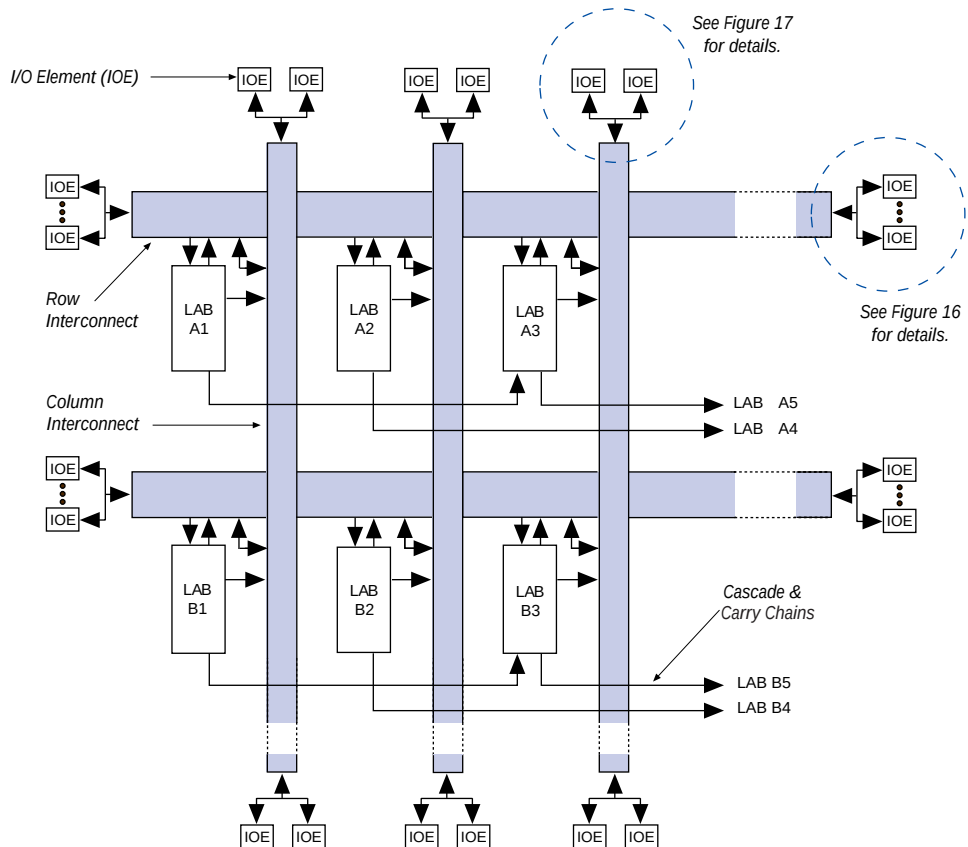
Clear & Preset Logic Control

Logic for the programmable register's clear and preset functions is controlled by the DATA3, LABCTRL1, and LABCTRL2 inputs to the LE. The clear and preset control structure of the LE asynchronously loads signals into a register. Either LABCTRL1 or LABCTRL2 can control the asynchronous clear. Alternatively, the register can be set up so that LABCTRL1 implements an asynchronous load. The data to be loaded is driven to DATA3; when LABCTRL1 is asserted, DATA3 is loaded into the register.

During compilation, the Altera Compiler automatically selects the best control signal implementation. Because the clear and preset functions are active-low, the Compiler automatically assigns a logic high to an unused clear or preset.

The clear and preset logic is implemented in one of the following six modes chosen during design entry:

- Asynchronous clear
- Asynchronous preset
- Asynchronous clear and preset
- Asynchronous load with clear
- Asynchronous load with preset
- Asynchronous load without clear or preset

Figure 14. FLEX 10KE Interconnect Resources

I/O Element

An IOE contains a bidirectional I/O buffer and a register that can be used either as an input register for external data that requires a fast setup time, or as an output register for data that requires fast clock-to-output performance. In some cases, using an LE register for an input register will result in a faster setup time than using an IOE register. IOEs can be used as input, output, or bidirectional pins. For bidirectional registered I/O implementation, the output register should be in the IOE, and the data input and output enable registers should be LE registers placed adjacent to the bidirectional pin. The Altera Compiler uses the programmable inversion option to invert signals from the row and column interconnect automatically where appropriate. [Figure 15](#) shows the bidirectional I/O registers.

IEEE Std. 1149.1 (JTAG) Boundary-Scan Support

All FLEX 10KE devices provide JTAG BST circuitry that complies with the IEEE Std. 1149.1-1990 specification. FLEX 10KE devices can also be configured using the JTAG pins through the BitBlaster or ByteBlasterMV download cable, or via hardware that uses the Jam™ STAPL programming and test language. JTAG boundary-scan testing can be performed before or after configuration, but not during configuration. FLEX 10KE devices support the JTAG instructions shown in [Table 15](#).

Table 15. FLEX 10KE JTAG Instructions

JTAG Instruction	Description
SAMPLE/PRELOAD	Allows a snapshot of signals at the device pins to be captured and examined during normal device operation, and permits an initial data pattern to be output at the device pins.
EXTEST	Allows the external circuitry and board-level interconnections to be tested by forcing a test pattern at the output pins and capturing test results at the input pins.
BYPASS	Places the 1-bit bypass register between the TDI and TD0 pins, which allows the BST data to pass synchronously through a selected device to adjacent devices during normal device operation.
USERCODE	Selects the user electronic signature (USERCODE) register and places it between the TDI and TD0 pins, allowing the USERCODE to be serially shifted out of TD0.
IDCODE	Selects the IDCODE register and places it between TDI and TD0, allowing the IDCODE to be serially shifted out of TD0.
ICR Instructions	These instructions are used when configuring a FLEX 10KE device via JTAG ports with a BitBlaster or ByteBlasterMV download cable, or using a Jam File (.jam) or Jam Byte-Code File (.jbc) via an embedded processor.

The instruction register length of FLEX 10KE devices is 10 bits. The USERCODE register length in FLEX 10KE devices is 32 bits; 7 bits are determined by the user, and 25 bits are pre-determined. [Tables 16](#) and [17](#) show the boundary-scan register length and device IDCODE information for FLEX 10KE devices.

Table 16. FLEX 10KE Boundary-Scan Register Length

Device	Boundary-Scan Register Length
EPF10K30E	690
EPF10K50E EPF10K50S	798
EPF10K100E	1,050
EPF10K130E	1,308
EPF10K200E EPF10K200S	1,446

Figure 20 shows the timing requirements for the JTAG signals.

Figure 20. FLEX 10KE JTAG Waveforms

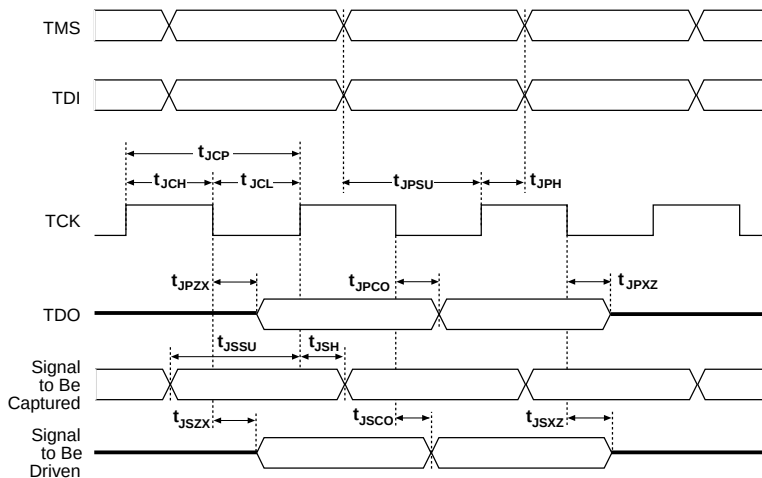


Table 18 shows the timing parameters and values for FLEX 10KE devices.

Table 18. FLEX 10KE JTAG Timing Parameters & Values

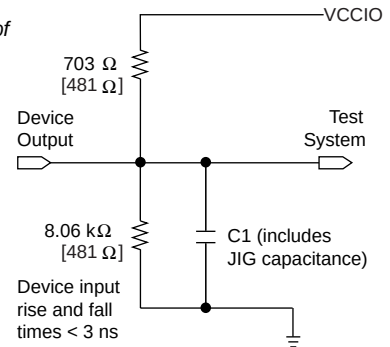
Symbol	Parameter	Min	Max	Unit
t_{JCP}	TCK clock period	100		ns
t_{JCH}	TCK clock high time	50		ns
t_{JCL}	TCK clock low time	50		ns
t_{JPSU}	JTAG port setup time	20		ns
t_{JPH}	JTAG port hold time	45		ns
t_{JPCO}	JTAG port clock to output		25	ns
t_{JPZX}	JTAG port high impedance to valid output		25	ns
t_{JPXZ}	JTAG port valid output to high impedance		25	ns
t_{JSSU}	Capture register setup time	20		ns
t_{JSH}	Capture register hold time	45		ns
t_{JSCO}	Update register clock to output		35	ns
t_{JSZX}	Update register high impedance to valid output		35	ns
t_{JSXZ}	Update register valid output to high impedance		35	ns

Generic Testing

Each FLEX 10KE device is functionally tested. Complete testing of each configurable static random access memory (SRAM) bit and all logic functionality ensures 100% yield. AC test measurements for FLEX 10KE devices are made under conditions equivalent to those shown in [Figure 21](#). Multiple test patterns can be used to configure devices during all stages of the production flow.

Figure 21. FLEX 10KE AC Test Conditions

Power supply transients can affect AC measurements. Simultaneous transitions of multiple outputs should be avoided for accurate measurement. Threshold tests must not be performed under AC conditions. Large-amplitude, fast-ground-current transients normally occur as the device outputs discharge the load capacitances. When these transients flow through the parasitic inductance between the device ground pin and the test system ground, significant reductions in observable noise immunity can result. Numbers in brackets are for 2.5-V devices or outputs. Numbers without brackets are for 3.3-V devices or outputs.



Operating Conditions

[Tables 19](#) through [23](#) provide information on absolute maximum ratings, recommended operating conditions, DC operating conditions, and capacitance for 2.5-V FLEX 10KE devices.

Table 19. FLEX 10KE 2.5-V Device Absolute Maximum Ratings *Note (1)*

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage	With respect to ground (2)	–0.5	3.6	V
V_{CCIO}			–0.5	4.6	V
V_I	DC input voltage		–2.0	5.75	V
I_{OUT}	DC output current, per pin		–25	25	mA
T_{STG}	Storage temperature	No bias	–65	150	°C
T_{AMB}	Ambient temperature	Under bias	–65	135	°C
T_J	Junction temperature	PQFP, TQFP, BGA, and FineLine BGA packages, under bias		135	°C
		Ceramic PGA packages, under bias		150	°C

Table 27. EAB Timing Macroparameters *Note (1), (6)*

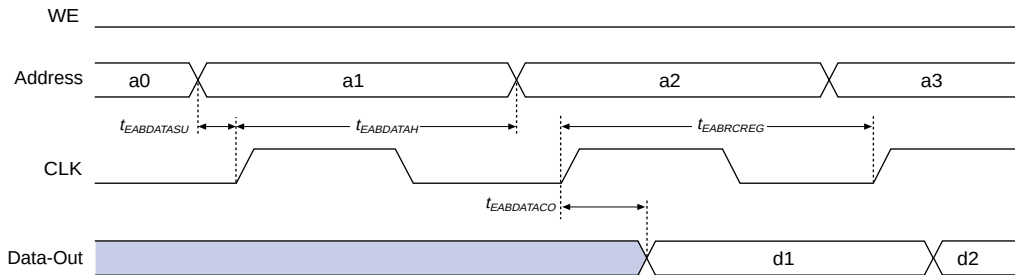
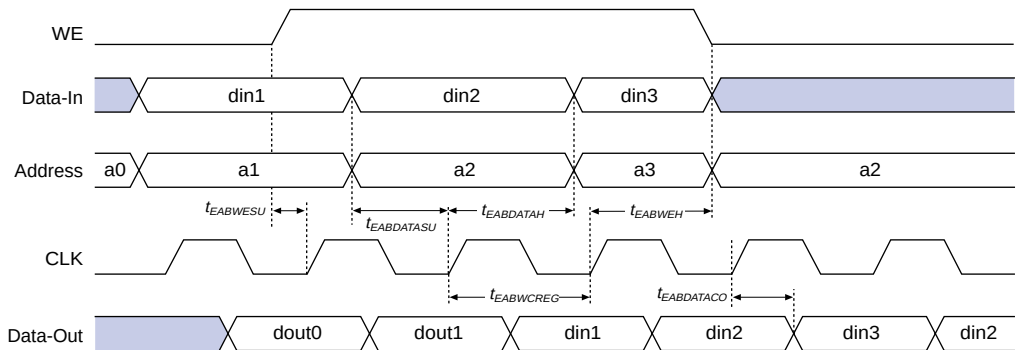
Symbol	Parameter	Conditions
t_{EABAA}	EAB address access delay	
$t_{EABRCCOMB}$	EAB asynchronous read cycle time	
$t_{EABRCREG}$	EAB synchronous read cycle time	
t_{EABWP}	EAB write pulse width	
$t_{EABWCCOMB}$	EAB asynchronous write cycle time	
$t_{EABWCREG}$	EAB synchronous write cycle time	
t_{EABDD}	EAB data-in to data-out valid delay	
$t_{EABDATAO}$	EAB clock-to-output delay when using output registers	
$t_{EABDATASU}$	EAB data/address setup time before clock when using input register	
$t_{EABDATAH}$	EAB data/address hold time after clock when using input register	
$t_{EABWESU}$	EAB WE setup time before clock when using input register	
t_{EABWEH}	EAB WE hold time after clock when using input register	
$t_{EABWDSU}$	EAB data setup time before falling edge of write pulse when not using input registers	
t_{EABWDH}	EAB data hold time after falling edge of write pulse when not using input registers	
$t_{EABWASU}$	EAB address setup time before rising edge of write pulse when not using input registers	
t_{EABWAH}	EAB address hold time after falling edge of write pulse when not using input registers	
t_{EABWO}	EAB write enable to data output valid delay	

Table 28. Interconnect Timing Microparameters *Note (1)*

Symbol	Parameter	Conditions
$t_{DIN2IOE}$	Delay from dedicated input pin to IOE control input	(7)
t_{DIN2LE}	Delay from dedicated input pin to LE or EAB control input	(7)
$t_{DCLK2IOE}$	Delay from dedicated clock pin to IOE clock	(7)
$t_{DCLK2LE}$	Delay from dedicated clock pin to LE or EAB clock	(7)
$t_{DIN2DATA}$	Delay from dedicated input or clock to LE or EAB data	(7)
$t_{SAMELAB}$	Routing delay for an LE driving another LE in the same LAB	
$t_{SAMEROW}$	Routing delay for a row IOE, LE, or EAB driving a row IOE, LE, or EAB in the same row	(7)
$t_{SAMECOLUMN}$	Routing delay for an LE driving an IOE in the same column	(7)
$t_{DIFFROW}$	Routing delay for a column IOE, LE, or EAB driving an LE or EAB in a different row	(7)
$t_{TROWROWS}$	Routing delay for a row IOE or EAB driving an LE or EAB in a different row	(7)
$t_{LEPERIPH}$	Routing delay for an LE driving a control signal of an IOE via the peripheral control bus	(7)
$t_{LABCARRY}$	Routing delay for the carry-out signal of an LE driving the carry-in signal of a different LE in a different LAB	
$t_{LABCASC}$	Routing delay for the cascade-out signal of an LE driving the cascade-in signal of a different LE in a different LAB	

Table 29. External Timing Parameters

Symbol	Parameter	Conditions
t_{DRR}	Register-to-register delay via four LEs, three row interconnects, and four local interconnects	(8)
t_{INSU}	Setup time with global clock at IOE register	(9)
t_{INH}	Hold time with global clock at IOE register	(9)
t_{OUTCO}	Clock-to-output delay with global clock at IOE register	(9)
t_{PCISU}	Setup time with global clock for registers used in PCI designs	(9),(10)
t_{PCIH}	Hold time with global clock for registers used in PCI designs	(9),(10)
t_{PCICO}	Clock-to-output delay with global clock for registers used in PCI designs	(9),(10)

Figure 30. EAB Synchronous Timing Waveforms**EAB Synchronous Read****EAB Synchronous Write (EAB Output Registers Used)**

Tables 31 through 37 show EPF10K30E device internal and external timing parameters.

Table 31. EPF10K30E Device LE Timing Microparameters (Part 1 of 2) *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.7		0.8		1.1	ns
t_{CLUT}		0.5		0.6		0.8	ns
t_{RLUT}		0.6		0.7		1.0	ns
t_{PACKED}		0.3		0.4		0.5	ns
t_{EN}		0.6		0.8		1.0	ns
t_{CICO}		0.1		0.1		0.2	ns
t_{CGEN}		0.4		0.5		0.7	ns

Table 40. EPF10K50E Device EAB Internal Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		1.7		2.0		2.7	ns
$t_{EABDATA1}$		0.6		0.7		0.9	ns
t_{EABWE1}		1.1		1.3		1.8	ns
t_{EABWE2}		0.4		0.4		0.6	ns
t_{EABRE1}		0.8		0.9		1.2	ns
t_{EABRE2}		0.4		0.4		0.6	ns
t_{EABCLK}		0.0		0.0		0.0	ns
t_{EABCO}		0.3		0.3		0.5	ns
$t_{EABYPASS}$		0.5		0.6		0.8	ns
t_{EABSU}	0.9		1.0		1.4		ns
t_{EABH}	0.4		0.4		0.6		ns
t_{EABCLR}	0.3		0.3		0.5		ns
t_{AA}		3.2		3.8		5.1	ns
t_{WP}	2.5		2.9		3.9		ns
t_{RP}	0.9		1.1		1.5		ns
t_{WDSU}	0.9		1.0		1.4		ns
t_{WDH}	0.1		0.1		0.2		ns
t_{WASU}	1.7		2.0		2.7		ns
t_{WAH}	1.8		2.1		2.9		ns
t_{RASU}	3.1		3.7		5.0		ns
t_{RAH}	0.2		0.2		0.3		ns
t_{WO}		2.5		2.9		3.9	ns
t_{DD}		2.5		2.9		3.9	ns
t_{EABOUT}		0.5		0.6		0.8	ns
t_{EABCH}	1.5		2.0		2.5		ns
t_{EABCL}	2.5		2.9		3.9		ns

Table 53. EPF10K130E Device IOE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{OD3}		4.0		5.6		7.5	ns
t_{XZ}		2.8		4.1		5.5	ns
t_{ZX1}		2.8		4.1		5.5	ns
t_{ZX2}		2.8		4.1		5.5	ns
t_{ZX3}		4.0		5.6		7.5	ns
t_{INREG}		2.5		3.0		4.1	ns
t_{IOFD}		0.4		0.5		0.6	ns
t_{INCOMB}		0.4		0.5		0.6	ns

Table 54. EPF10K130E Device EAB Internal Microparameters (Part 1 of 2) *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		1.5		2.0		2.6	ns
$t_{EABDATA2}$		0.0		0.0		0.0	ns
t_{EABWE1}		1.5		2.0		2.6	ns
t_{EABWE2}		0.3		0.4		0.5	ns
t_{EABRE1}		0.3		0.4		0.5	ns
t_{EABRE2}		0.0		0.0		0.0	ns
t_{EABCLK}		0.0		0.0		0.0	ns
t_{EABCO}		0.3		0.4		0.5	ns
$t_{EABYPASS}$		0.1		0.1		0.2	ns
t_{EABSU}	0.8		1.0		1.4		ns
t_{EABH}	0.1		0.2		0.2		ns
t_{EABCLR}	0.3		0.4		0.5		ns
t_{AA}		4.0		5.0		6.6	ns
t_{WP}	2.7		3.5		4.7		ns
t_{RP}	1.0		1.3		1.7		ns
t_{WDSU}	1.0		1.3		1.7		ns
t_{WDH}	0.2		0.2		0.3		ns
t_{WASU}	1.6		2.1		2.8		ns
t_{WAH}	1.6		2.1		2.8		ns
t_{RASU}	3.0		3.9		5.2		ns
t_{RAH}	0.1		0.1		0.2		ns
t_{WO}		1.5		2.0		2.6	ns

Table 61. EPF10K200E Device EAB Internal Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		2.0		2.4		3.2	ns
$t_{EABDATA1}$		0.4		0.5		0.6	ns
t_{EABWE1}		1.4		1.7		2.3	ns
t_{EABWE2}		0.0		0.0		0.0	ns
t_{EABRE1}		0		0		0	ns
t_{EABRE2}		0.4		0.5		0.6	ns
t_{EABCLK}		0.0		0.0		0.0	ns
t_{EABCO}		0.8		0.9		1.2	ns
$t_{EABYPASS}$		0.0		0.1		0.1	ns
t_{EABSU}	0.9		1.1		1.5		ns
t_{EABH}	0.4		0.5		0.6		ns
t_{EABCLR}	0.8		0.9		1.2		ns
t_{AA}		3.1		3.7		4.9	ns
t_{WP}	3.3		4.0		5.3		ns
t_{RP}	0.9		1.1		1.5		ns
t_{WDSU}	0.9		1.1		1.5		ns
t_{WDH}	0.1		0.1		0.1		ns
t_{WASU}	1.3		1.6		2.1		ns
t_{WAH}	2.1		2.5		3.3		ns
t_{RASU}	2.2		2.6		3.5		ns
t_{RAH}	0.1		0.1		0.2		ns
t_{WO}		2.0		2.4		3.2	ns
t_{DD}		2.0		2.4		3.2	ns
t_{EABOUT}		0.0		0.1		0.1	ns
t_{EABCH}	1.5		2.0		2.5		ns
t_{EABCL}	3.3		4.0		5.3		ns

Table 62. EPF10K200E Device EAB Internal Timing Macroparameters (Part 1 of 2) *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{EABAA}		5.1		6.4		8.4	ns
$t_{EABRCOMB}$	5.1		6.4		8.4		ns
$t_{EABRCREG}$	4.8		5.7		7.6		ns
t_{EABWP}	3.3		4.0		5.3		ns

Table 69. EPF10K50S Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{EABAA}		3.7		5.2		7.0	ns
$t_{EABRCCOMB}$	3.7		5.2		7.0		ns
$t_{EABRCREG}$	3.5		4.9		6.6		ns
t_{EABWP}	2.0		2.8		3.8		ns
$t_{EABWCCOMB}$	4.5		6.3		8.6		ns
$t_{EABWCREG}$	5.6		7.8		10.6		ns
t_{EABDD}		3.8		5.3		7.2	ns
$t_{EABDATACO}$		0.8		1.1		1.5	ns
$t_{EABDATASU}$	1.1		1.6		2.1		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	0.7		1.0		1.3		ns
t_{EABWEH}	0.4		0.6		0.8		ns
$t_{EABWDSU}$	1.2		1.7		2.2		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	1.6		2.3		3.0		ns
t_{EABWAH}	0.9		1.2		1.8		ns
t_{EABWO}		3.1		4.3		5.9	ns

Table 70. EPF10K50S Device Interconnect Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		3.1		3.7		4.6	ns
t_{DIN2LE}		1.7		2.1		2.7	ns
$t_{DIN2DATA}$		2.7		3.1		5.1	ns
$t_{DCLK2IOE}$		1.6		1.9		2.6	ns
$t_{DCLK2LE}$		1.7		2.1		2.7	ns
$t_{SAMELAB}$		0.1		0.1		0.2	ns
$t_{SAMEROW}$		1.5		1.7		2.4	ns
$t_{SAMECOLUMN}$		1.0		1.3		2.1	ns
$t_{DIFFROW}$		2.5		3.0		4.5	ns
$t_{TWOROWS}$		4.0		4.7		6.9	ns
$t_{LEPERIPH}$		2.6		2.9		3.4	ns
$t_{LABCARRY}$		0.1		0.2		0.2	ns
$t_{LABCASC}$		0.8		1.0		1.3	ns

Table 71. EPF10K50S External Timing Parameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{DDR}		8.0		9.5		12.5	ns
$t_{\text{INSU}}^{(2)}$	2.4		2.9		3.9		ns
$t_{\text{INH}}^{(2)}$	0.0		0.0		0.0		ns
$t_{\text{OUTCO}}^{(2)}$	2.0	4.3	2.0	5.2	2.0	7.3	ns
$t_{\text{INSU}}^{(3)}$	2.4		2.9				ns
$t_{\text{INH}}^{(3)}$	0.0		0.0				ns
$t_{\text{OUTCO}}^{(3)}$	0.5	3.3	0.5	4.1			ns
t_{PCISU}	2.4		2.9		—		ns
t_{PCIH}	0.0		0.0		—		ns
t_{PCICO}	2.0	6.0	2.0	7.7	—	—	ns

Table 72. EPF10K50S External Bidirectional Timing Parameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{\text{INSUBIDIR}}^{(2)}$	2.7		3.2		4.3		ns
$t_{\text{INHBIDIR}}^{(2)}$	0.0		0.0		0.0		ns
$t_{\text{INHBIDIR}}^{(3)}$	0.0		0.0		—		ns
$t_{\text{INSUBIDIR}}^{(3)}$	3.7		4.2		—		ns
$t_{\text{OUTCOBIDIR}}^{(2)}$	2.0	4.5	2.0	5.2	2.0	7.3	ns
$t_{\text{XZBIDIR}}^{(2)}$		6.8		7.8		10.1	ns
$t_{\text{ZXBIDIR}}^{(2)}$		6.8		7.8		10.1	ns
$t_{\text{OUTCOBIDIR}}^{(3)}$	0.5	3.5	0.5	4.2	—	—	
$t_{\text{XZBIDIR}}^{(3)}$		6.8		8.4		—	ns
$t_{\text{ZXBIDIR}}^{(3)}$		6.8		8.4		—	ns

Notes to tables:

- (1) All timing parameters are described in [Tables 24 through 30](#).
- (2) This parameter is measured without use of the ClockLock or ClockBoost circuits.
- (3) This parameter is measured with use of the ClockLock or ClockBoost circuits

Table 73. EPF10K200S Device Internal & External Timing Parameters*Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.7		0.8		1.2	ns
t_{CLUT}		0.4		0.5		0.6	ns
t_{RLUT}		0.5		0.7		0.9	ns
t_{PACKED}		0.4		0.5		0.7	ns
t_{EN}		0.6		0.5		0.6	ns
t_{CICO}		0.1		0.2		0.3	ns
t_{CGEN}		0.3		0.4		0.6	ns
t_{CGENR}		0.1		0.2		0.3	ns
t_{CASC}		0.7		0.8		1.2	ns
t_C		0.5		0.6		0.8	ns
t_{CO}		0.5		0.6		0.8	ns
t_{COMB}		0.3		0.6		0.8	ns
t_{SU}	0.4		0.6		0.7		ns
t_H	1.0		1.1		1.5		ns
t_{PRE}		0.4		0.6		0.8	ns
t_{CLR}		0.5		0.6		0.8	ns
t_{CH}	2.0		2.5		3.0		ns
t_{CL}	2.0		2.5		3.0		ns

Table 74. EPF10K200S Device IOE Timing Microparameters (Part 1 of 2)*Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{IOD}		1.8		1.9		2.6	ns
t_{IOC}		0.3		0.3		0.5	ns
t_{IOCO}		1.7		1.9		2.6	ns
t_{IOCOMB}		0.5		0.6		0.8	ns
t_{IOSU}	0.8		0.9		1.2		ns
t_{IOH}	0.4		0.8		1.1		ns
t_{IOCLR}		0.2		0.2		0.3	ns
t_{OD1}		1.3		0.7		0.9	ns
t_{OD2}		0.8		0.2		0.4	ns
t_{OD3}		2.9		3.0		3.9	ns
t_{XZ}		5.0		5.3		7.1	ns
t_{ZX1}		5.0		5.3		7.1	ns

Table 76. EPF10K200S Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{EABAA}		3.9		6.4		8.4	ns
$t_{EABRCOMB}$	3.9		6.4		8.4		ns
$t_{EABRCREG}$	3.6		5.7		7.6		ns
t_{EABWP}	2.1		4.0		5.3		ns
$t_{EABWCOMB}$	4.8		8.1		10.7		ns
$t_{EABWCREG}$	5.4		8.0		10.6		ns
t_{EABDD}		3.8		5.1		6.7	ns
$t_{EABDATAO}$		0.8		1.0		1.3	ns
$t_{EABDATASU}$	1.1		1.6		2.1		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	0.7		1.1		1.5		ns
t_{EABWEH}	0.4		0.5		0.6		ns
$t_{EABWDSU}$	1.2		1.8		2.4		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	1.9		3.6		4.7		ns
t_{EABWAH}	0.8		0.5		0.7		ns
t_{EABWO}		3.1		4.4		5.8	ns

Table 77. EPF10K200S Device Interconnect Timing Microparameters (Part 1 of 2) *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		4.4		4.8		5.5	ns
t_{DIN2LE}		0.6		0.6		0.9	ns
$t_{DIN2DATA}$		1.8		2.1		2.8	ns
$t_{DCLK2IOE}$		1.7		2.0		2.8	ns
$t_{DCLK2LE}$		0.6		0.6		0.9	ns
$t_{SAMELAB}$		0.1		0.1		0.2	ns
$t_{SAMEROW}$		3.0		4.6		5.7	ns
$t_{SAMECOLUMN}$		3.5		4.9		6.4	ns
$t_{DIFFROW}$		6.5		9.5		12.1	ns
$t_{TROWROWS}$		9.5		14.1		17.8	ns
$t_{LEPERIPH}$		5.5		6.2		7.2	ns
$t_{LABCARRY}$		0.3		0.1		0.2	ns

Device Pin-Outs

See the Altera web site (<http://www.altera.com>) or the Altera Digital Library for pin-out information.

Revision History

The information contained in the *FLEX 10KE Embedded Programmable Logic Data Sheet* version 2.5 supersedes information published in previous versions.

Version 2.5

The following changes were made to the *FLEX 10KE Embedded Programmable Logic Data Sheet* version 2.5:

- *Note (1)* added to *Figure 23*.
- Text added to “I/O Element” section on *page 34*.
- Updated *Table 22*.

Version 2.4

The following changes were made to the *FLEX 10KE Embedded Programmable Logic Data Sheet* version 2.4: updated text on *page 34* and *page 63*.



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